Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8513	non-volatile semiconductor memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:37
L2	69300	flash memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:37
L3	1282897	controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:38
L4	59316	voltage generator or voltage generation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:39
L5	1	voltage generation control register	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:39
L6	1609365	processing circuit or central processing circuit or CPU or I3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:43
L7	38359	data register	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:43
L8	16777	decision circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:43

L9	232	determined control data	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:44
L10	560179	random access memory or RAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:45
L11	235168	semiconductor substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:45
L12	86715	semiconductor integrated circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:49
L13	2473	l1 and l2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:49
L14	257	l13 and l4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:49
L15	142	l14 and l6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:49
L16	13	l15 and l7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:49

L17	3	I16 and I8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:50
L19	1	I17 and I10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:52
L20	108030	control data	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:50
L21	1	I17 and I20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:50
L22	788	compar$3 and (reference voltage with generated voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:53
L25	12	I22 and I8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 22:54
L28	12	I25 and (I1 or I2 or I4 or I6 or I7 or I20)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:12
L29	22065	714/724 or 714/736 or 714/740 or 714/799 or 714/699 or 714/819 or 714/? or 365/? or 711/?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:04

L30	5211	frequency dividing circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:04
L31	27420	oscillation circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:04
L32	13344	oscillation signal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:05
L33	32	load$3 and (test program with semiconductor integrated circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:06
L34	2268	l31 and l32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:07
L35	1	l34 and l33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:07
L36	115	l30 and l34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:07
L38	3	l36 and l7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:08

L39	3	I38 and I20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:09
L40	3	I39 and I6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:10
L42	1	I40 and I2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/04 23:10